

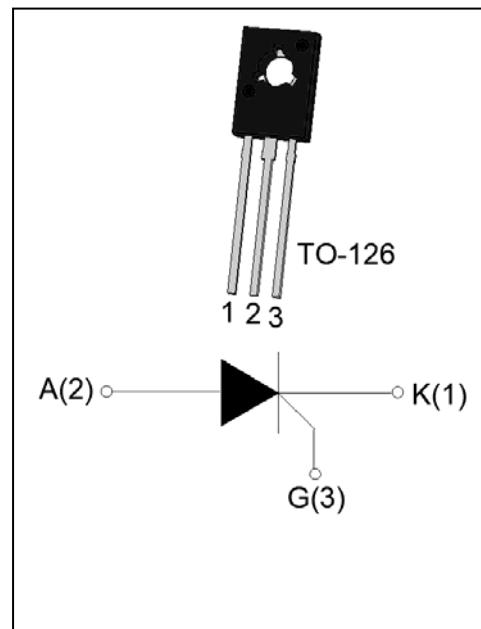


JX040Q 4A Sensitive SCR

Rev.A.1.0

DESCRIPTION:

The JX040Q SCR provides high dV/dt rate with strong resistance to electromagnetic interface. It is especially recommended for use on residual current circuit breaker, straight hair, igniter etc. Package TO-126 is RoHS compliant.



MAIN FEATURES

Symbol	Value	Unit
$I_{T(RMS)}$	4	A
V_{DRM} / V_{RRM}	600	V
I_{GT}	≤ 200	μA

ABSOLUTE MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
Storage junction temperature range	T_{stg}	-40-150	°C
Operating junction temperature range	T_j	-40-125 ^①	°C
Repetitive peak off-state voltage ($T_j=25^\circ C$)	V_{DRM}	600	V
Repetitive peak reverse voltage ($T_j=25^\circ C$)	V_{RRM}	600	V
Average on-state current ($T_c \leq 84^\circ C$)	$I_{T(AV)}$	2.5	A
RMS on-state current ($T_c \leq 84^\circ C$)	$I_{T(RMS)}$	4	A
Non repetitive surge peak on-state current ($t_p=10ms, T_j=25^\circ C$)	I_{TSM}	40	A
Non repetitive surge peak on-state current ($t_p=8.3ms, T_j=25^\circ C$)		44	
I^2t value for fusing ($t_p=10ms, T_j=25^\circ C$)	I^2t	8	A^2s
Critical rate of rise of on-state current ($I_G=2 \times I_{GT}, f=100Hz, T_j=125^\circ C$)	dI/dt	50	$A/\mu s$
Peak gate current ($t_p=20\mu s, T_j=125^\circ C$)	I_{GM}	2	A
Average gate power dissipation ($T_j=125^\circ C$)	$P_{G(AV)}$	0.5	W

Peak gate power	P_{GM}	5	W
Peak pulse voltage ($T_j=25^\circ C$; non-repetitive, off-state; FIG.7)	V_{pp}	0.5	kV

NOTE 1: When we parallel connect a $\leq 1K\Omega$ resistor between Gate and Cathode, the T_j can reach $125^\circ C$; if without this resistor, the T_j only can reach $110^\circ C$.

ELECTRICAL CHARACTERISTICS ($T_j=25^\circ C$ unless otherwise specified)

Symbol	Test Condition	Value			Unit
		MIN.	TYP.	MAX.	
I_{GT}	$V_D=12V R_L=33\Omega$	-	50	200	μA
V_{GT}		-	0.6	0.8	V
V_{GD}	$V_D=V_{DRM} T_j=125^\circ C$	0.2	-	-	V
I_L	$I_G=1.2 I_{GT}$	-	-	6	mA
I_H	$I_T=0.05A$	-	-	5	mA
dV/dt	$V_D=400V T_j=125^\circ C R_{GK}=1K\Omega$	50	-	-	V/ μs
	$V_D=400V T_j=125^\circ C R_{GK}=220\Omega$	200	-	-	
t_{on}	$I_G=10mA I_A=20mA I_R=2mA T_j=25^\circ C$	-	2	-	μs
t_{off}		-	50	-	μs

STATIC CHARACTERISTICS

Symbol	Parameter		Value(MAX.)	Unit
V_{TM}	$I_T=8A t_p=380\mu s$	$T_j=25^\circ C$	1.6	V
V_{TO}	Threshold voltage	$T_j=125^\circ C$	0.8	V
R_D	Dynamic Resistance	$T_j=125^\circ C$	0.1	Ω
I_{DRM}	$V_D=V_{DRM} V_R=V_{RRM}$	$T_j=25^\circ C$	5	μA
I_{RRM}		$T_j=125^\circ C$	0.5	mA

THERMAL RESISTANCES

Symbol	Parameter	Value	Unit
$R_{th(j-c)}$	junction to case (DC)	7.5	$^\circ C/W$
$R_{th(j-a)}$	junction to ambient (DC)	120	$^\circ C/W$

ORDERING INFORMATION

<u>J</u>	<u>X</u>	<u>040</u>	<u>Q</u>
JieJie Microelectronics Co.,Ltd.			
	Sensitive gate SCRs		
		<u>I_T(RMS):4A</u>	<u>Q:TO-126</u>

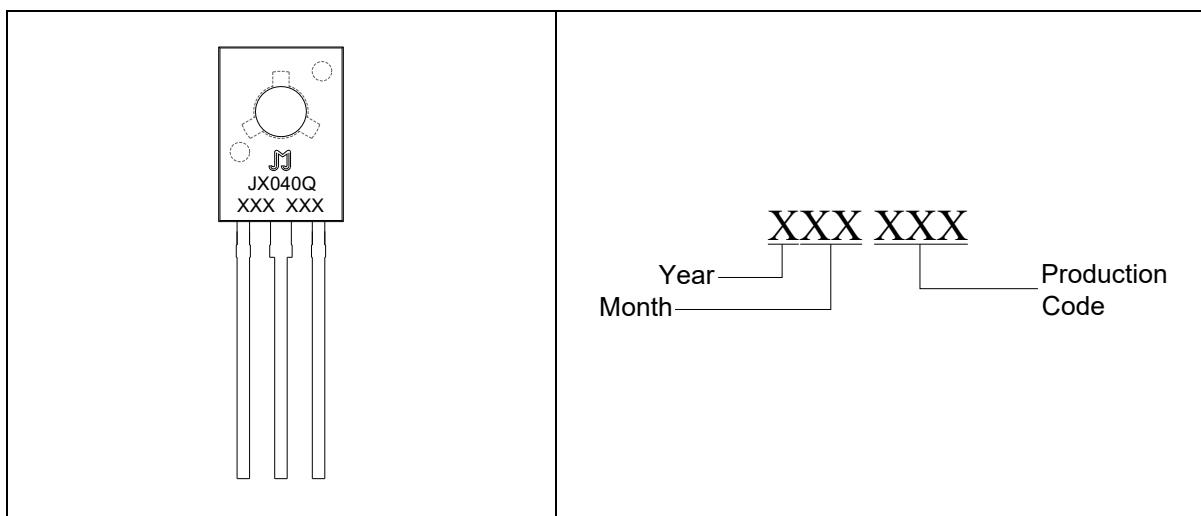
MARKING

FIG.1 Maximum power dissipation versus RMS on-state current

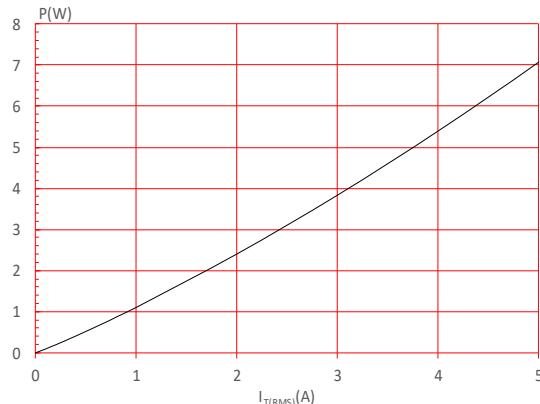


FIG.3: Surge peak on-state current versus number of cycles

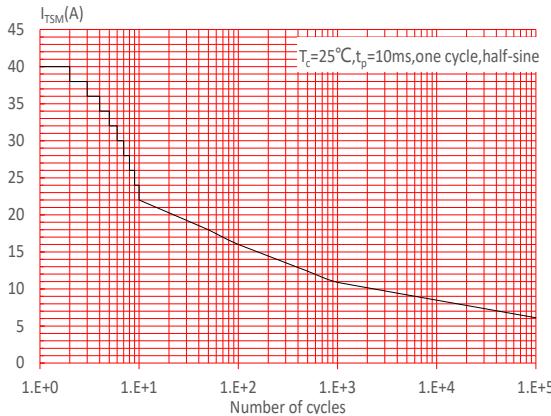


FIG.5: Non-repetitive surge peak on-state current for a sinusoidal pulse with width $t_p < 10\text{ms}$, and corresponding value of I^2t ($\text{d}I/\text{dt} < 50\text{A}/\mu\text{s}$)

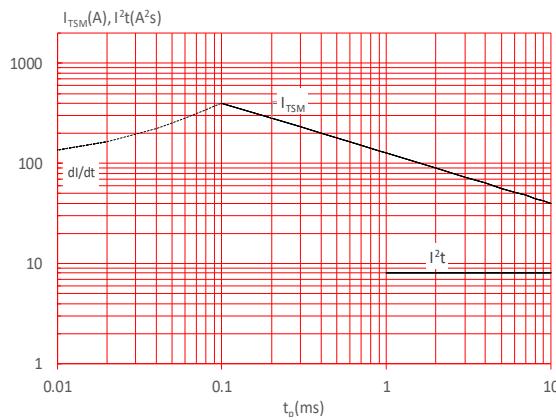


FIG.2: RMS on-state current versus case temperature

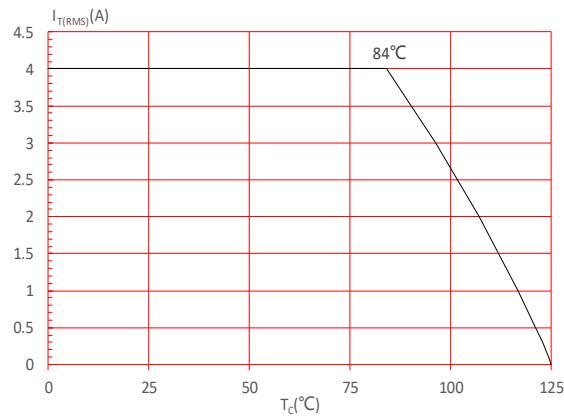


FIG.4: On-state characteristics

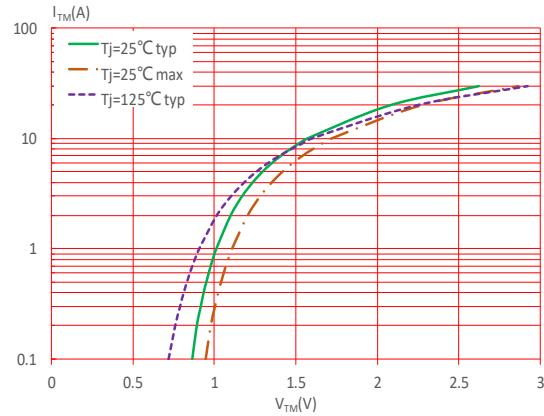


FIG.6: Relative variations of gate triggercurrent, holding current and latching current versus junction temperature

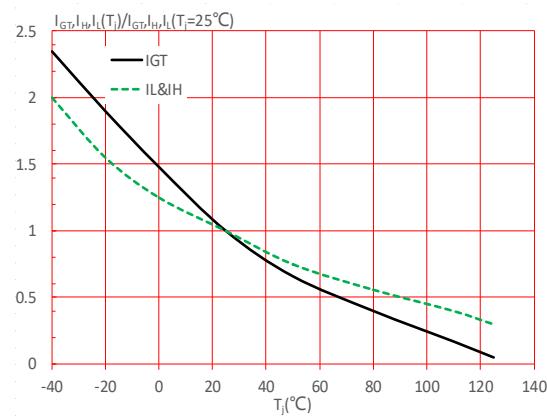
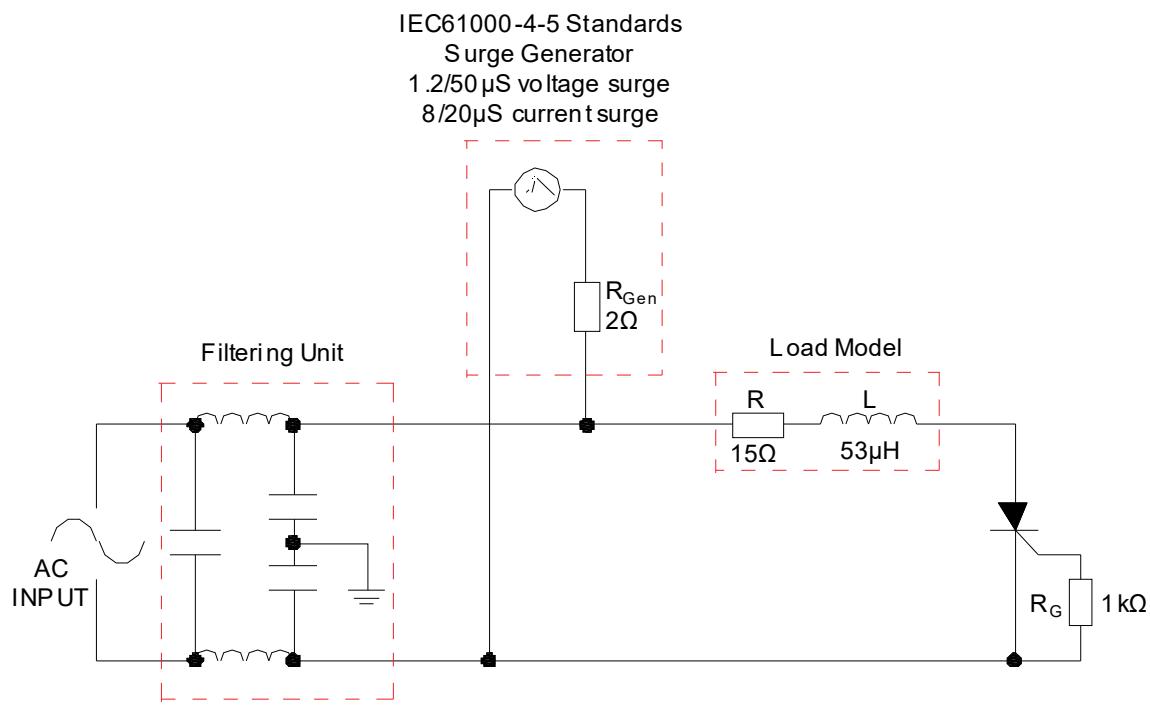


FIG.7: Test circuit for inductive and resistive loads to IEC-61000-4-5 standards.



SHAPING AND SOLDERING PARAMETERS

Refer to 《Instructions for installation of plastic-sealed in-line power devices》 released by JieJie

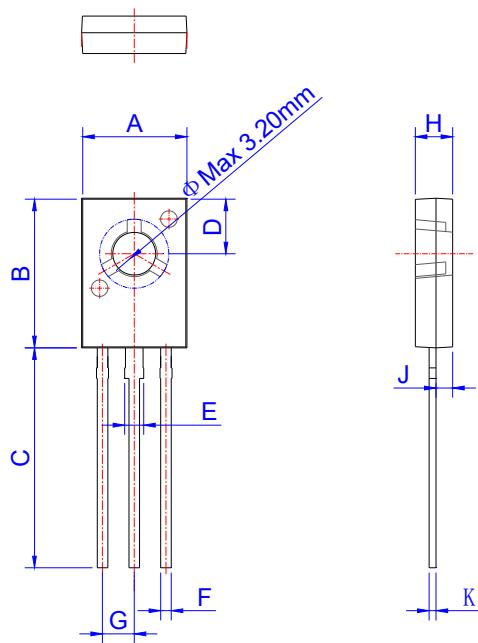
ORDERING INFORMATION

Order code	Voltage V_{DRM}/V_{RRM} (V)	IGT(μA)	Package	Base qty. (pcs)	Delivery mode
JX040Q	600	≤ 200	TO-126	500	Bulk Pack

Document Revision History

Date	Revision	Changes
Apr.12, 2023	A.1.0	Last update

PACKAGE MECHANICAL DATA



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	7.40		7.80	0.291		0.307
B	10.6		11.2	0.417		0.441
C	15.3		16.3	0.602		0.642
D	3.90		4.10	0.154		0.161
E	1.17		1.47	0.046		0.058
F	0.66		0.86	0.026		0.034
G	2.15		2.45	0.085		0.096
H	2.50		2.90	0.098		0.114
J	1.10		1.50	0.043		0.059
K	0.45		0.60	0.018		0.024

DELIVERY MODE

PACKAGE	OUTLINE	BAG (PCS)	INNER BOX (PCS)	CARTON BOX (PCS)
TO-126	Bulk Pack	500	2,000	10,000

Information furnished in this document is believed to be accurate and reliable. However, Jiangsu JieJie Microelectronics Co., Ltd. assumes no responsibility for the consequences of use without consideration for such information nor use beyond it. Information mentioned in this document is subject to change without notice, apart from that when an agreement is signed, Jiangsu JieJie complies with the agreement. Products and information provided in this document have no infringement of patents. Jiangsu JieJie assumes no responsibility for any infringement of other rights of third parties which may result from the use of such products and information. This document supersedes and replaces all information previously supplied.

 is a registered trademark of Jiangsu JieJie Microelectronics Co., Ltd.

Copyright ©2023 Jiangsu JieJie Microelectronics Co., Ltd. Printed All rights reserved.